

# RAA207703GBM/7704GBM/7705GBM

## Synchronous Buck Regulator with Internal Power MOSFETs

R07DS0892EJ0001  
Rev.0.01  
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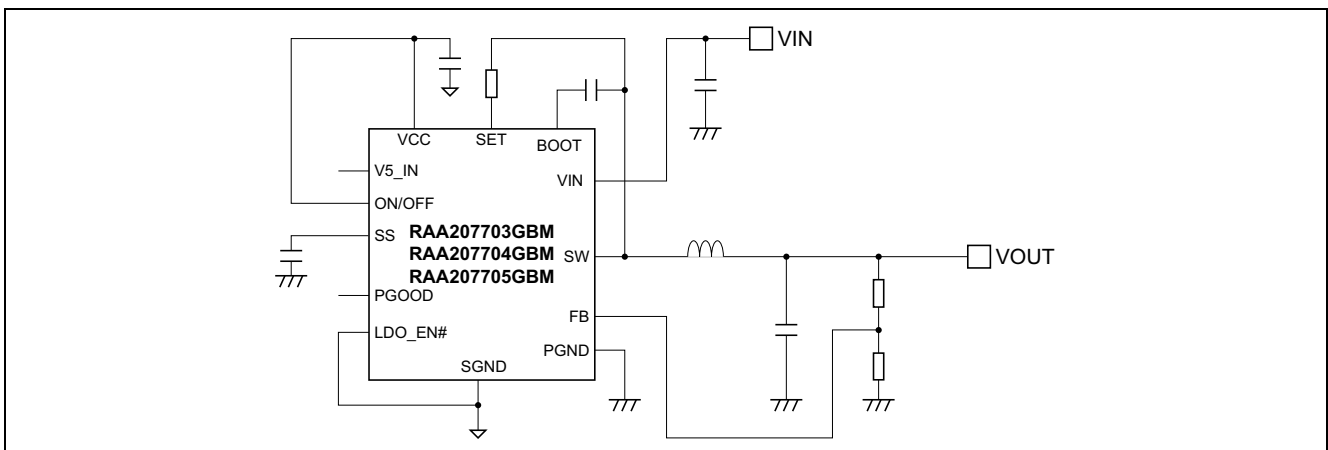
### Description

The RAA207703GBM is monolithic synchronous buck regulator with power MOSFETs in extremely small package. The RAA207703GBM delivers high output current by small  $R_{ds(on)}$  Power MOSFETs. Constant on time control architecture provides fast transient response, and minimize external components. The RAA207703GBM operates skip mode at light load, it provides high efficiency in all load condition. The RAA207703GBM incorporates internal 5V LDO, so the regulator can operate single power supply. Three current ability products can be selected.

### Features

- Input voltage range: 5.5 V to 16 V
- Constant-On-Time control
- Built-in power MOSFETs suitable for PC, Server application
- Internal 5 V LDO for single power supply operation
- 5 V LDO / external 5 V input selectable (LDO remote ON/OFF)
- Switching frequency: Adjustable up to 2 MHz
- High average output current, up to 15 A (7703GBM), 10 A (7704GBM), 5 A (7705GBM)
- Controllable driver: Remote on/off
- Power Good function
- Over current protection/Over voltage protection/Thermal shutdown function
- Built-in bootstrapping diode
- Soft Start period adjustable
- Enhanced light load mode function for higher efficiency
- Extremely small chip size package with solder bump
- Pb-Free/Halogen-Free

### Application Circuit



Pin Arrangement

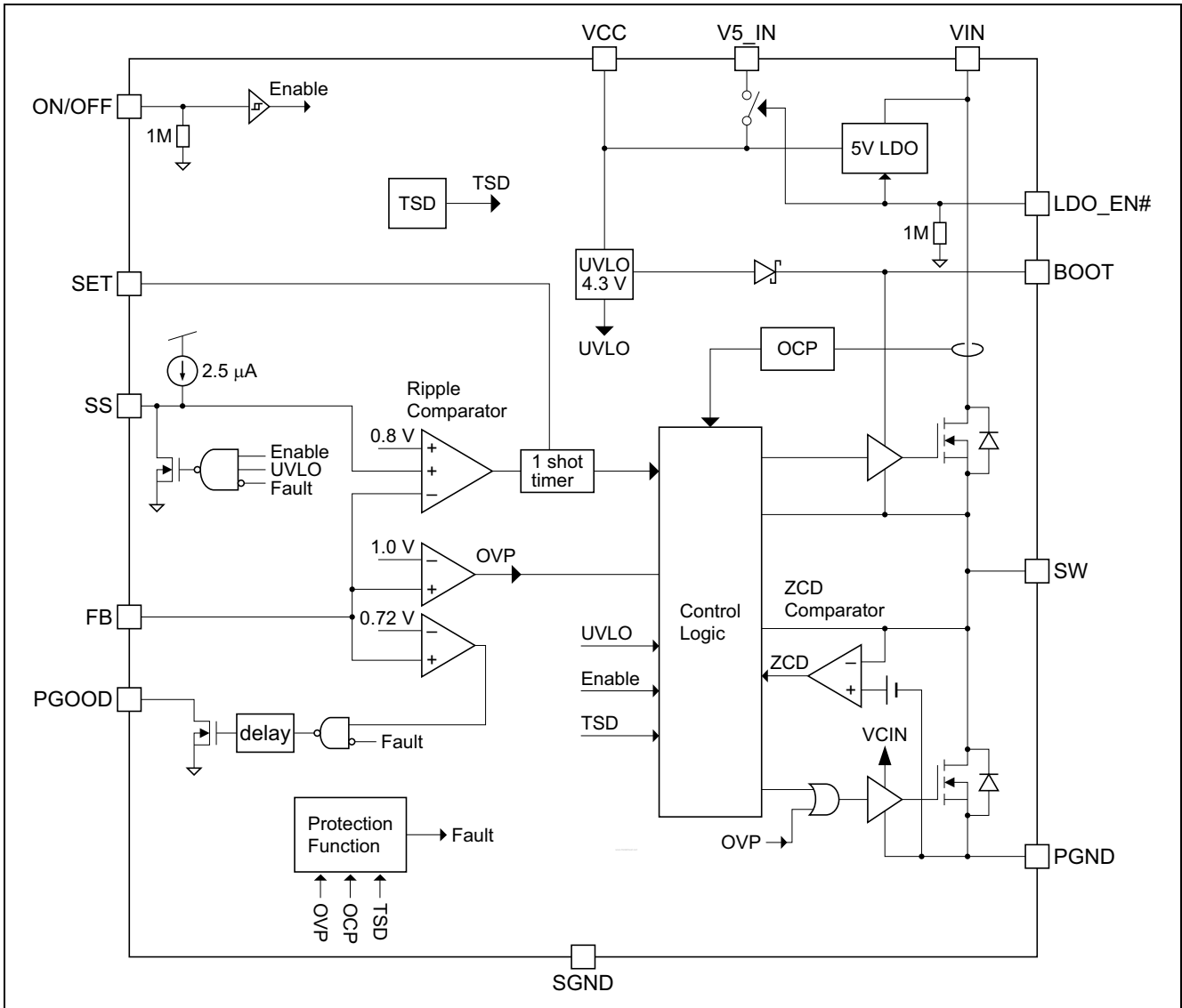


**Pin Description**

Pin Name	Pin No.	Description	Remarks
VCC	1A	Controller voltage	Controller supply input (5 V regulator output)
SGND	2A	Controller analog GND	Should be connected to PGND on PCB pattern
FB	3A	Feedback voltage input pin	
V5_IN	4A	5 V external input	
LDO_EN#	5A	Internal 5 V LDO enable pin	
BOOT	1B	Bootstrap voltage pin	To be supplied +5 V through integrated SBD
SET	2B	Constant on time program pin	Tie resistor between SW and SET
PGOOD	3B	Power good indicator pin	Pull low when No Good (open drain output)
SS	4B	Soft start period program pin	Tie capacitor between SS and SGND
ON/OFF	5B	Operation enable pin	Operation stop when L signal asserted
VIN	—	Input voltage	
SW	—	Switching node	
PGND	—	Power ground	Should be connected to SGND on PCB pattern

Note: Pin assign of 1A-5A & 1B-5B is common through RAA207703GBM, RAA207704GBM and RAA207705GBM.

Block Diagram



1. Truth table for the ON/OFF pin

ON/OFF Input	Driver Chip Status
"L"	Shutdown (operation STOP)
"Open"	Shutdown (operation STOP)
"H"	Enable (Normal operation)

2. Truth table for LDO\_EN# pin

LDO_EN# Input	5 V Regulator Status
"L"	LDO enable
"Open"	LDO enable
"H"	LDO disable

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit	Notes
Input voltage	VIN	-0.3 to +20	V	1
Switch node voltage	SW	20(DC), 23(<10 ns)	V	1
BOOT voltage	VBOOT	25(DC), 28(<10 ns)	V	1, 2
Controller voltage	VCC	-0.3 to +6	V	1
VCC current	ICC	-20 to +0.1	mA	3
V5_IN voltage	V5_IN	-0.3 to +6	V	1
FB pin voltage	VFB	-0.3 to VCC +0.3	V	1, 4
ON/OFF voltage	VON/OFF	-0.3 to VIN	V	1
LDO_EN# voltage	VLDO_EN#	-0.3 to VIN	V	1
SET voltage	VSET	-0.3 to VIN	V	1
PGOOD voltage	VPGOOD	-0.3 to VIN	V	1
PGOOD sink current	IPGOOD	+2	mA	3
Operating junction temperature	Tj-opr	-40 to +125	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. Rated voltages are relative to voltages on the SGND and PGND pins.

2. BOOT – VCIN < 20 V

3. For rated current, (+) indicates inflow to the chip and (-) indicates outflow.

4. VCC + 0.3 V < 6 V

## Recommended Operating Condition

Item	Symbol	Ratings	Unit	Remarks
Input voltage	VIN	5.5 to 16	V	When 5 V LDO use
Controller voltage	VCC	4.5 to 5.5	V	Controller voltage is supplied externally
Continuous output current	IOUT	0 to 15 0 to 10 0 to 5	A	15 A: RAA207703GBM 10 A: RAA207704GBM 5 A: RAA207705GBM

## Electrical Characteristics

(Ta = 25°C, VIN = 12 V, unless otherwise specified)

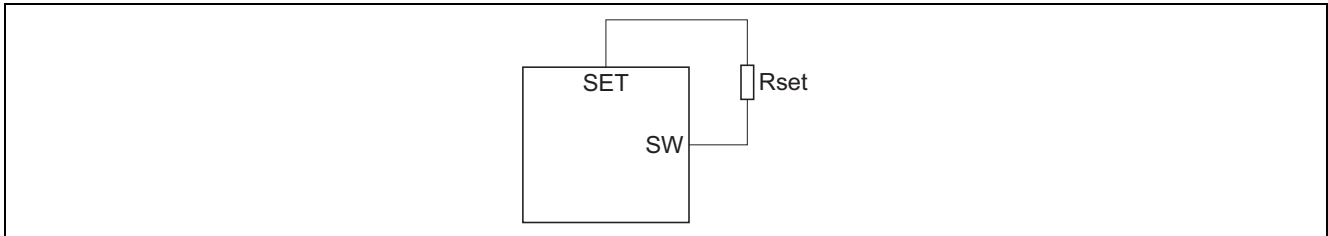
Item	Symbol	Min	Typ	Max	Unit	Test Conditions	
Supply	VIN start threshold	VH	—	4.3	4.6	V	
	VIN shutdown threshold in CCM	VL	3.6	3.8	—	V	
	VIN shutdown threshold in ELL mode	V <sub>LCCM</sub>	—	3.0	3.6	V	In ELL mode (DCM, f <sub>sw</sub> < 100 kHz)
	VIN quiescent current	I <sub>q</sub>	—	400	500	μA	Output = no load, ELL mode
	VIN disable current (LDO_EN# = 12 V)	I <sub>IN-DISBL1</sub>	—	70	150	μA	ON/OFF = 0 V, LDO_EN# = 12 V
	VIN disable current (LDO_EN# = 0 V)	I <sub>IN-DISBL2</sub>	—	130	200	μA	ON/OFF = 0 V, LDO_EN# = 0 V
Remote on/off	Disable level	V <sub>DISBL</sub>	—	—	0.6	V	3.3 / 5.0 V interface
	Enable level	V <sub>ENBL</sub>	2.0	—	—	V	
	Pull-down resistance	R <sub>DISBL</sub>	0.7	1	1.3	MΩ	ON/OFF = 1 V
5 V LDO enable	5 V LDO on level	V <sub>LDO_ON</sub>	—	—	0.6	V	
	5 V LDO off level	V <sub>LDO_OFF</sub>	2.0	—	—	V	
	Pull-down resistance	R <sub>LS_IN</sub>	0.7	1	1.3	MΩ	LDO_EN# = 1 V
5 V LDO output	5 V LDO output voltage	V <sub>LDO</sub>	4.5	5.0	5.5	V	VIN = 12 V
FB	Comparator threshold voltage	V <sub>FB_COMP</sub>	792	800	808	mV	
	FB input current	I <sub>FB_IN</sub>	-0.1	0	+0.1	μA	FB = 1 V
Power good indicator	Rising threshold on FB	V <sub>PG_rise</sub>	0.67	0.72	0.77	V	
	Power good hysteresis	dV <sub>PG</sub>	—	50	—	mV	
	Power good resistance	R <sub>PG</sub>	0.25	0.5	1	kΩ	FB = 0 V
Soft start	Soft start bias current	I <sub>SS</sub>	1.8	2.5	3.2	μA	
Over voltage protection	OVP trip voltage on FB	V <sub>OVP</sub>	0.95	1.00	1.05	V	
Over current protection	OCP trip current (RAA207703GBM)	I <sub>OCP</sub>	16.0	20.0	24.0	A	Fixed internally *1
	OCP trip current (RAA207704GBM)	I <sub>OCP</sub>	12.0	15.0	18.0	A	Fixed internally *1
	OCP trip current (RAA207705GBM)	I <sub>OCP</sub>	6.4	8.0	9.6	A	Fixed internally *1
Over temperature protection	TSD trip temperature	T <sub>TSD</sub>	130	150	—	°C	*1
	Temperature hysteresis	T <sub>hys</sub>	—	30	—	°C	*1

Note: \*1 Not directly tested. Assured by related characteristics test.

### Description of Operation

The RAA207703GBM operates as voltage-ripple based constant on time control architecture. Converter output is controlled by output voltage ripple which is determined by inductor ripple current and ESR & ESL of output capacitor. Each switching cycle starts High-side MOSFET turn on which time is decided by 1 shot timer. After High-side MOSFET turns off, Low side turns on, and it keeps until FB voltage becomes lower than reference voltage. In light load condition, Low-side MOSFET on time is decided by inductor zero current.

### Switching Frequency, Constant on Time Setting



Switching Frequency in CCM mode is determined by following equation.

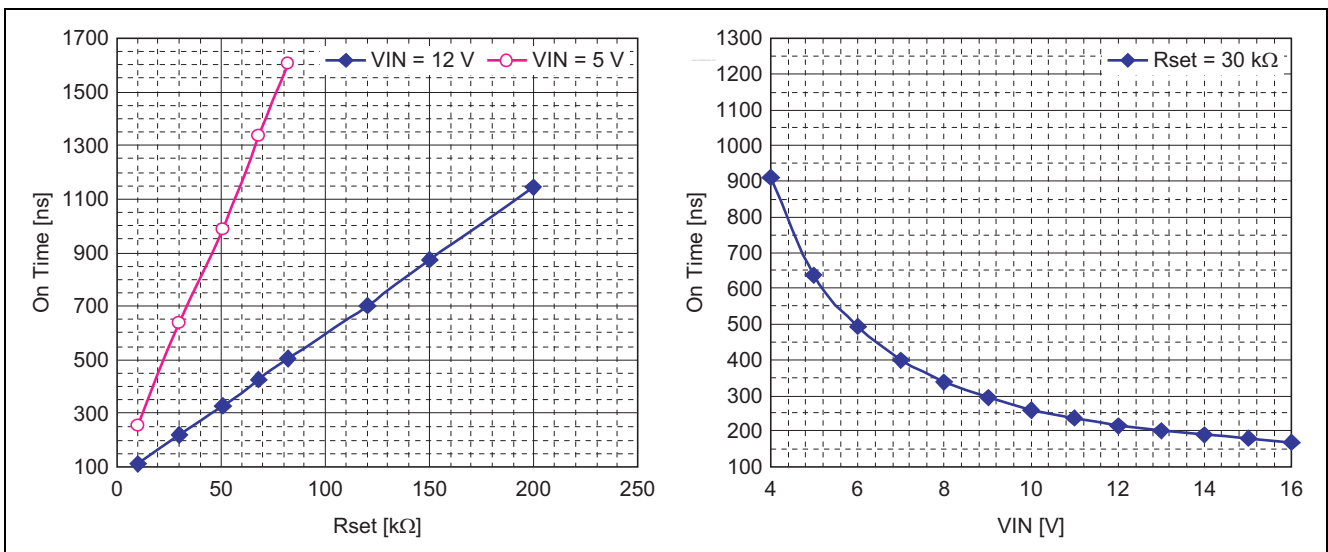
$$\text{Switching Frequency: } (V_o/V_{in}) \cdot (1/t_{on}) \text{ [Hz]}$$

Here,  $t_{on}$  is High-side MOS on time, and it is determined by following equation.

$$\text{On time pulse: } (5 \text{ pF} / V_{in} - 2.0 \text{ V}) \cdot R_{set} + 50 \text{ ns [s]}$$

From above equation, constant on time is change depend on  $V_{in}$ , so switching frequency is almost constant when  $V_{IN}$  change. This architecture is suitable for battery application. From the above equation,  $R_{set}$  is calculated by

$$R_{set: } (V_{out} / (V_{in} \cdot F_{sw}) - 50 \text{ ns}) \cdot (V_{in} - 2.0 \text{ V}) / (50 \text{ pF} \cdot 1 \text{ V}) \text{ [\Omega]}$$



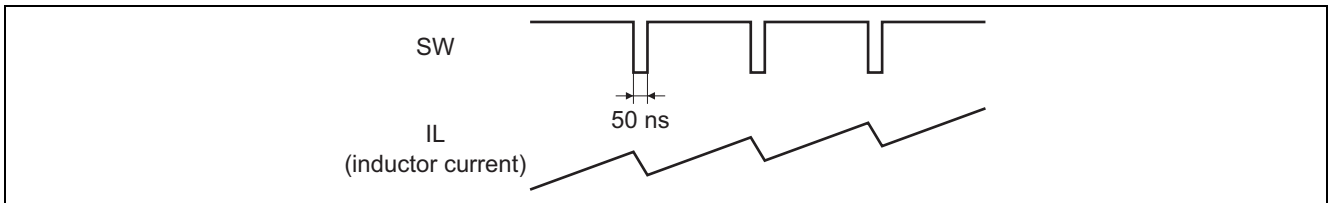
### Maximum Duty Cycle Operation

Maximum duty cycle is restricted by following equation.

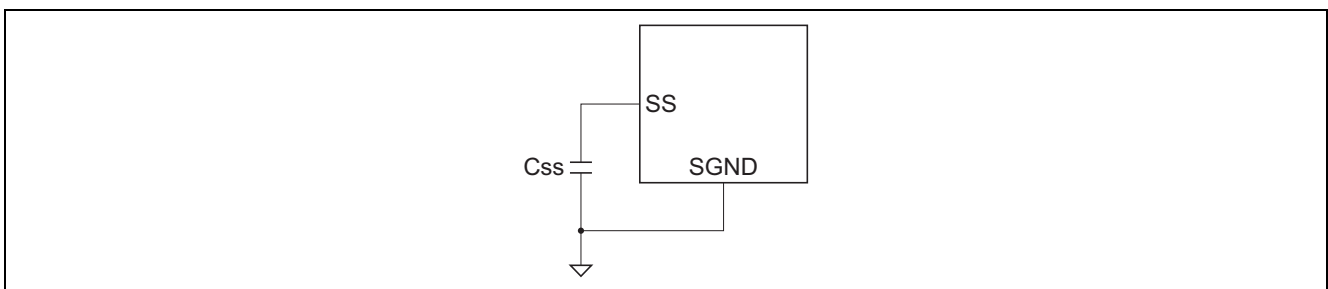
$$\text{Max. duty: } 1 - (50 \text{ ns} \cdot F_{sw})$$

Here,  $F_{sw}$  is switching frequency.

If FB voltage does not reach reference voltage after the High-side MOSFET turn on time is expired, Low-side MOSFET turns on 50 ns, and next switching cycle starts. Especially, this condition occurs when output load transient state.



### Soft Start



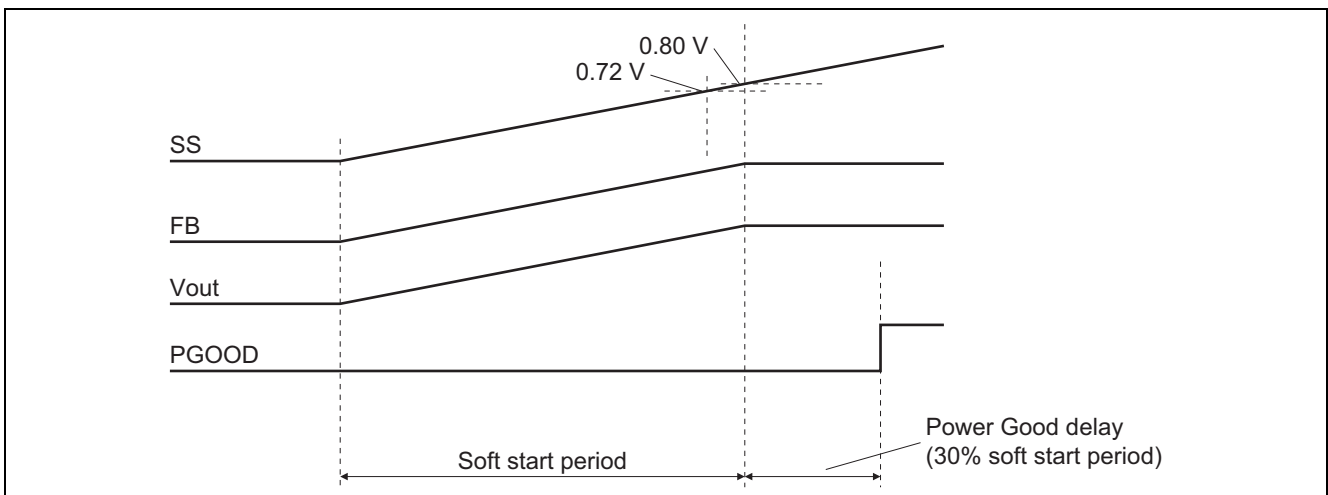
Soft start ramp period is adjustable by external capacitor ( $C_{ss}$ ) selection. When converter start operating,  $2 \mu\text{A}$  current from SS pin charges capacitor between SS and GND. Soft start period is determined by following equation.

$$\text{Soft Start period: } C_{ss} \cdot 0.8 \text{ V} / 2.5 \mu\text{A [s]}$$

Here,  $0.8 \text{ V}$  is internal reference voltage  $V_{ref}$ . IC operates diode emulation mode at Soft start period, so it can prevent from reverse current when pre-bias condition. Soft start restarts when Enable signal re-entered, and after OCP, OVP, TSD, UVL release condition.

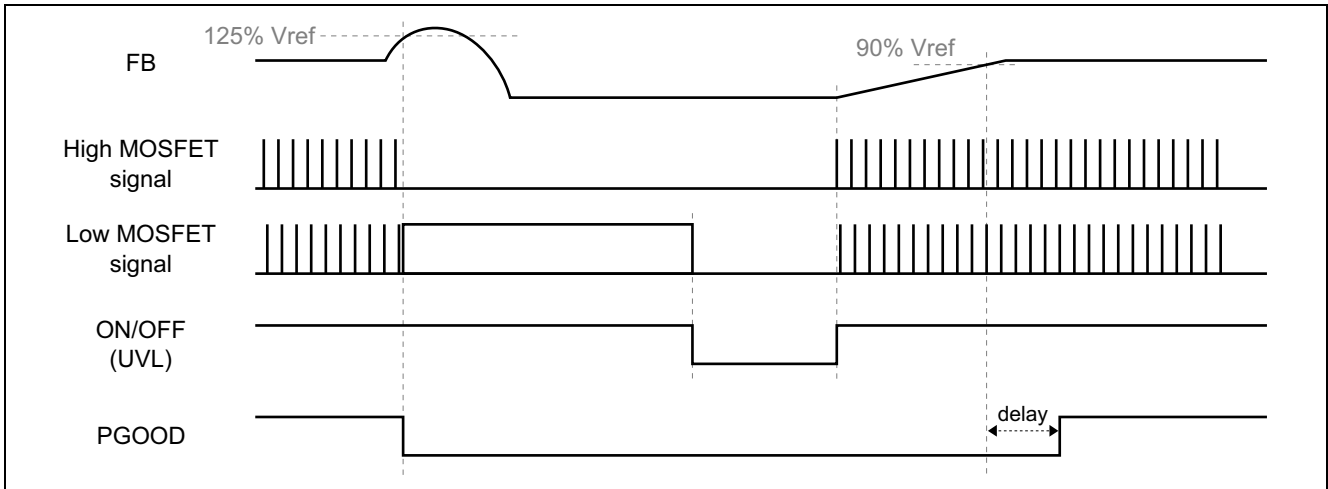
### Power Good Indicator

Power good indicator is useful for controlling multi-converter systems for sequential start up and shut down. FB voltage is monitored continuously by power good comparator. The power good comparator compares FB pin and 90% internal reference voltage ( $0.72 \text{ V}$ ). When FB reaches reference voltage, PGOOD pin becomes high impedance after internal delay (30% of soft start period). Under the fault condition (UVLO, OVP, OCP, TSD), PGOOD pin is pulled low.



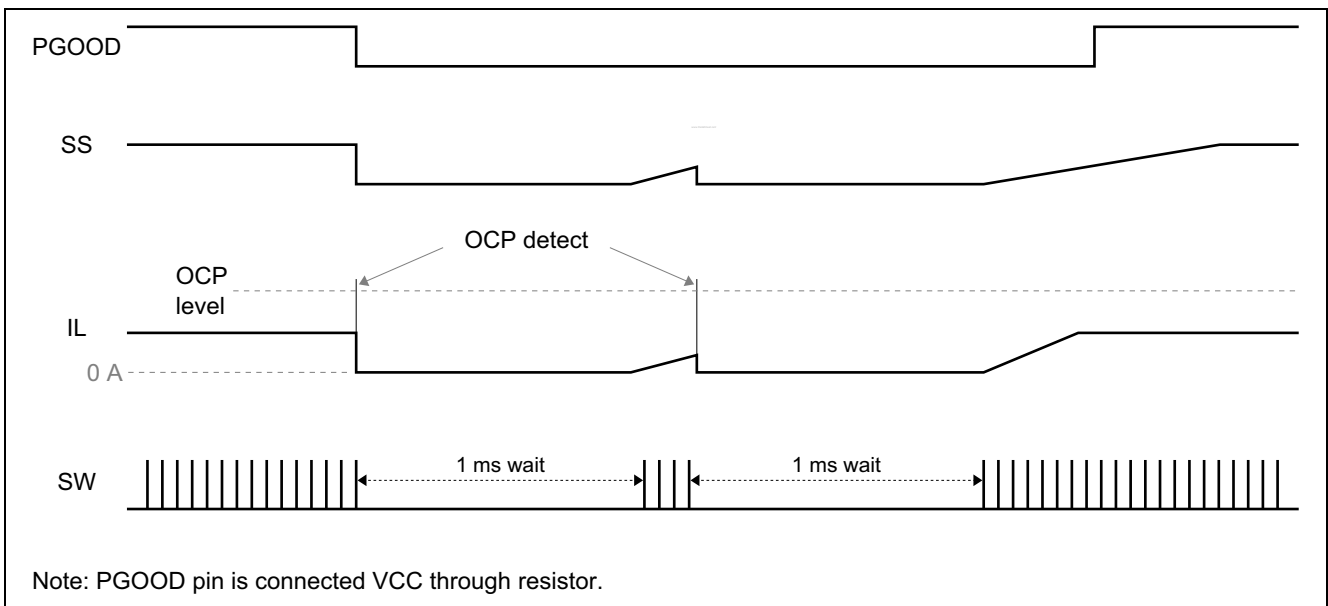
### Over Voltage Protection (OVP)

When FB voltage exceeds 125% of reference voltage (1.00 V), switching stops immediately and latched Low-side MOSFET on state in order to pull the output voltage. To leave the OVP condition, VCIN needs to be pulled under the UVLO level, and re-enter the signal.



### Over Current Protection (OCP)

OCP detection circuit monitors high-side MOSFET drain-source current. When the current exceeds fixed level eight time, IC starts hiccup operation. In the hiccup operation, switching stops and operate 1 ms timer. After 1 ms timer is expired, IC operates again from soft start state. If IC detect OCP in the soft start circuit, hiccup operation start again.



**Thermal Shutdown (TSD)**

Thermal sensor monitors junction temperature of IC. When junction temperature exceeds 150°C, switching stops. After junction temperature become 125°C, IC restart switching from soft start (Non-latched function).

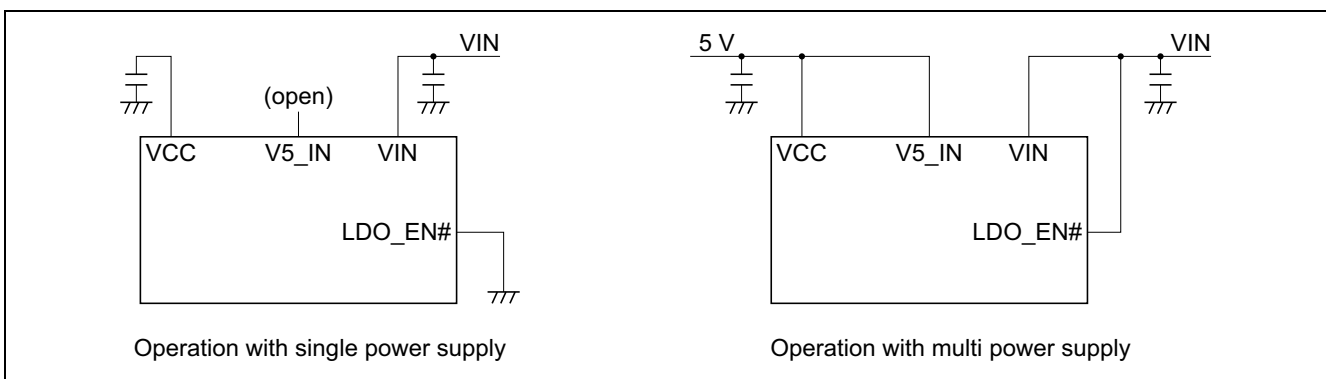
**Enhanced Light Load Function (ELL)**

IC operates diode emulation mode in light load condition. To enhance light load efficiency, IC detects light load condition automatically, and operate as Enhanced Light Load mode (ELL). In ELL mode, bias current of IC becomes small, so this function can improve the efficiency.

**Controller Power Supply**

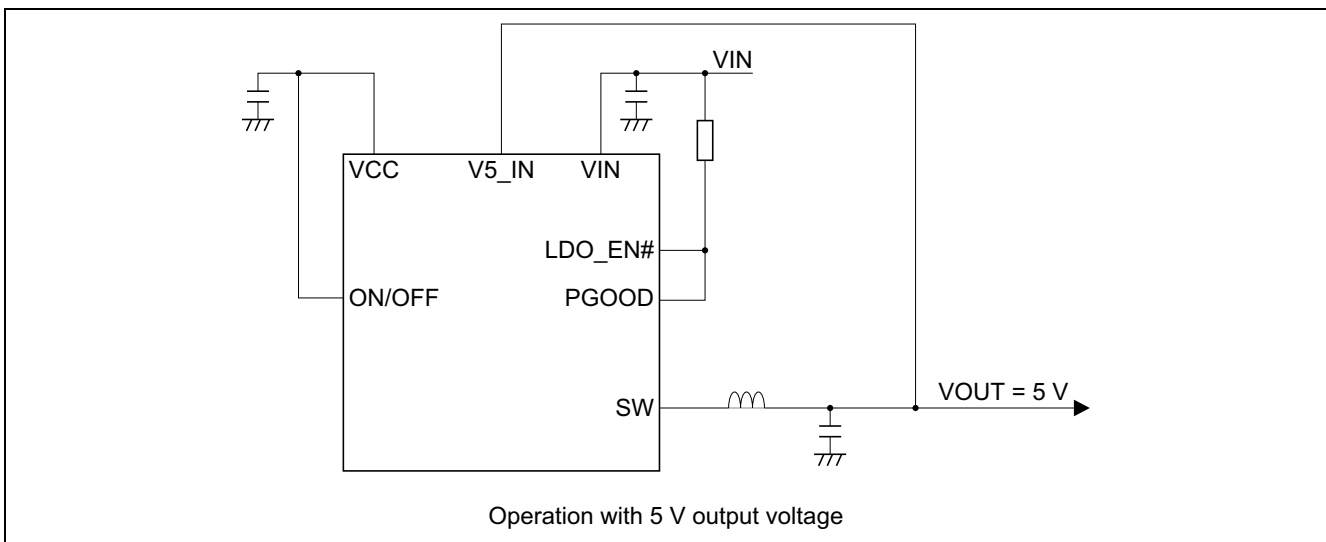
The RAA207703GBM incorporates internal 5 V LDO, so it can operate with single power supply. LDO\_EN# can control LDO operation, and select the controller power supply from LDO or V5\_IN pin. When LDO\_EN# = H state, external 5 V should be applied to V5\_IN pin.

Typical pin connection of each operation are below.



**LDO Loss Reduce Circuit (only for Vout = 5 V)**

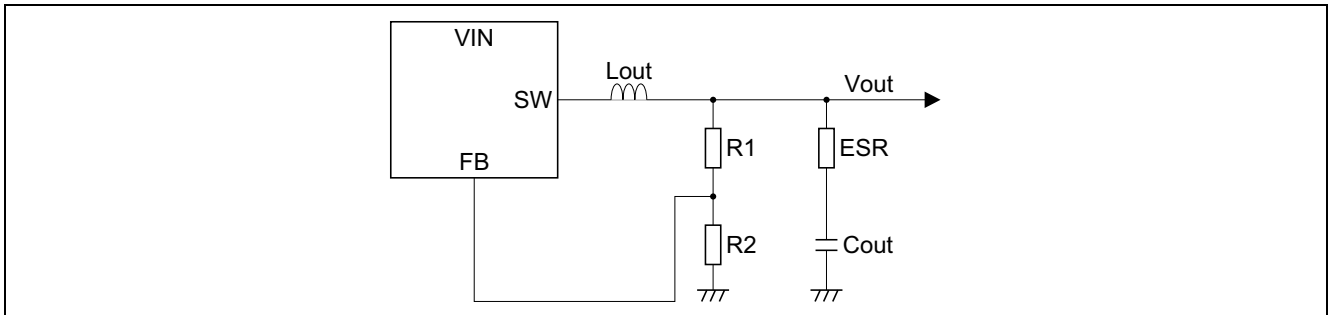
When regulator output is 5 V, IC can operate with their output voltage in order to reduce LDO loss. In this time, PGOOD signal can be used for LDO or 5V\_IN select signal. Pin connection is below.



Initially, controller voltage is supplied from VIN through internal LDO. Switching regulator starts from soft-start and power good output becomes hi-impedance when output 5 V becomes stable. After LDO\_EN# detects Hi level, LDO stops and controller operates their own 5 V output voltage.

### Stability Criteria, Output Voltage Setting for High ESR Output Capacitor

Small output ripple voltage makes control loop unstable in constant on time architecture. Ripple voltage needs to be larger than 15 mV on FB pin. When using high ESR (>50 mΩ) capacitor such as Electrolytic capacitor, Polymer aluminum capacitor for output capacitor, ripple voltage on FB pin will be more than 15 mV.



#### Stability criteria

From loop stability analysis, constant on time control system must satisfy below equation.

$$\text{Stability criteria: } ESR \cdot C_{out} > t_{on} / 2$$

Here,  $t_{on}$  is constant on time. If the system cannot satisfy above equation, subharmonic oscillation will occur.

#### Vout setting

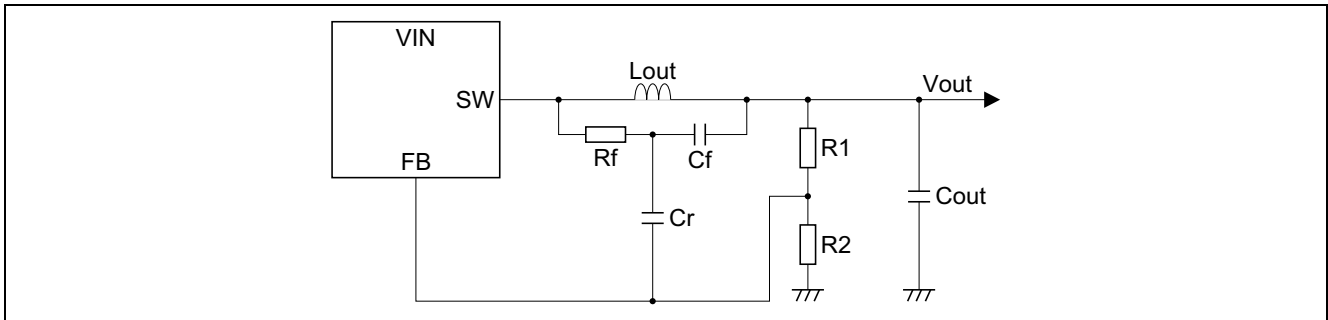
FB comparator compares FB voltage and internal accurate reference voltage (0.8 V). Feedback loop controls FB voltage to match the reference voltage. Therefore, output voltage is set by following equation.

$$V_{out}: 0.8 \text{ V} \cdot (R1+R2) / R2$$

Here, R1 and R2 is output voltage divider resistor (refer to above figure). However, ripple voltage on FB pin affects FB voltage, so Vout slightly shifts from setting value. If the system needs high accuracy, adjust Vout by changing R1, R2 value.

**Operating with Small ESR Output Capacitor**

When using low-ESR output capacitor like MLCC, voltage ripple on output voltage node is very small. So voltage ripple needs to be enhanced by additional components. Recommended ripple enhance method is like below figure.



**Ripple injection on FB pin**

Rf and Cf make ripple voltage using inductor DCR ripple. Cr is used for AC ripple injection to FB pin. Ripple voltage between Rf and Cf is described by following equation.

$$V_{ripple} = (V_{IN} - V_{OUT}) \cdot t_{on} / (R_f \cdot C_f)$$

Make sure above ripple voltage is larger than 15 mV.

**Stability criteria**

From loop stability analysis of above circuit configuration, the system must satisfy below equation.

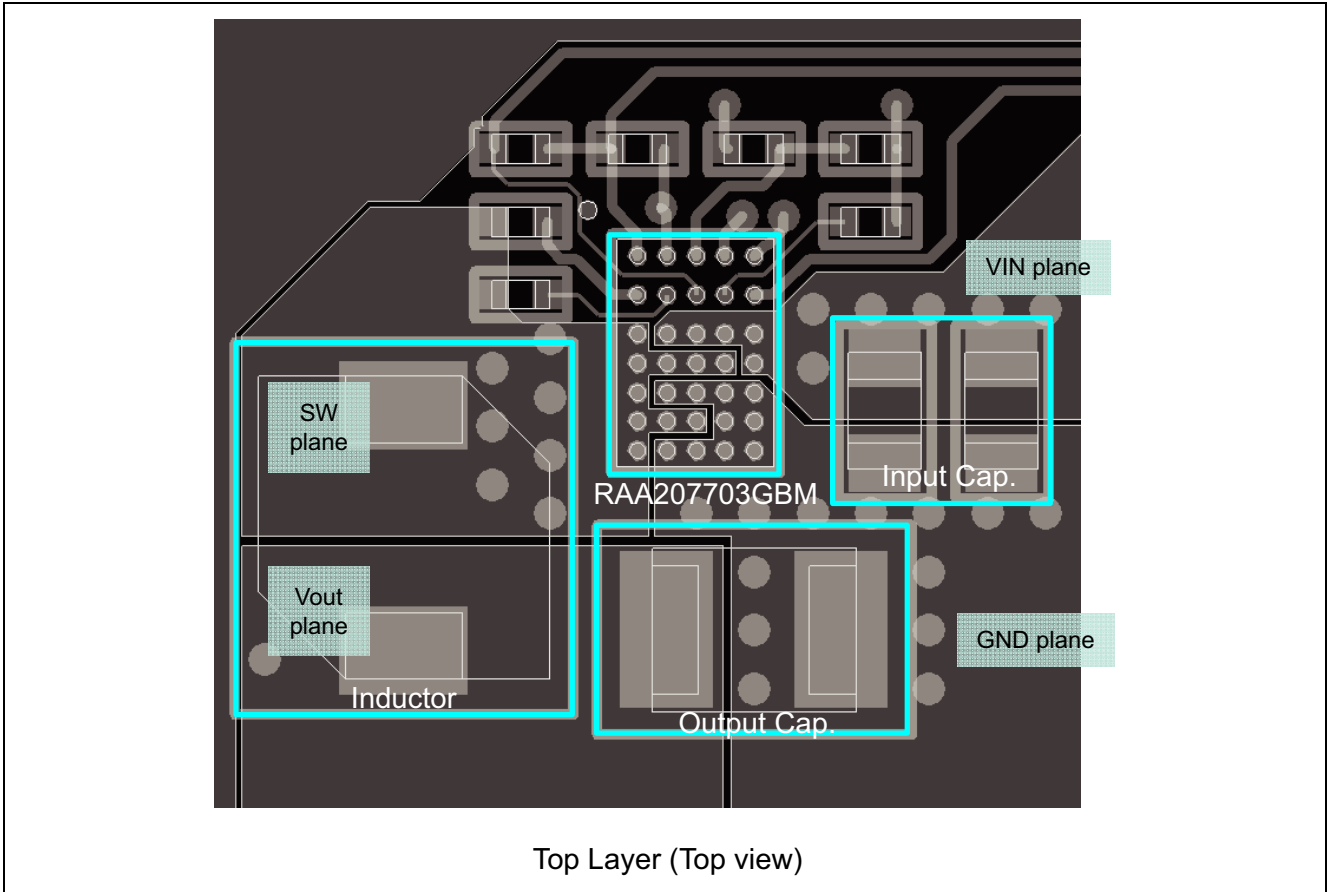
$$\text{Stability criteria: } L_{out} \cdot C_{out} / (R_f \cdot C_f) > t_{on} / 2$$

If the system cannot satisfy above equation, subharmonic oscillation will occur.

**Vout setting**

Output voltage setting is basically same concept as high ESR capacitor use case. Ripple voltage from injection circuit affects FB voltage, so it need to be adjust R1, R2 for high accuracy system.

### Board Layout Example (RAA207703GBM)



## Representative Inductors

Maker	Inductance [ $\mu\text{H}$ ]	$\Delta\text{L}/\text{L}_0 = 20\%$ Change [A]	Dimensions [mm]
NEC Tokin MPC series	0.42	20.0	6.7 × 8.0 × 4.0
	0.60	19.0	6.7 × 8.0 × 5.0
	0.88	24.0	10.0 × 11.5 × 4.0
	1.0	25.0	10.0 × 11.7 × 5.5
ALPS Green Device GLMC series	0.47	13.9 * <sup>1</sup>	6.5 × 7.4 × 3.0
	1.0	10 * <sup>1</sup>	6.5 × 7.4 × 3.0
	1.5	8.8 * <sup>1</sup>	6.5 × 7.4 × 3.0
TOKO FDVE0630 series	0.33	15.9	6.7 × 7.4 × 3.0
	0.47	15.6	6.7 × 7.4 × 3.0
	0.75	10.9	6.7 × 7.4 × 3.0
	1.0	9.5	6.7 × 7.4 × 3.0
TDK SPM5030 series	0.35	14.9	5.0 × 5.2 × 3.0
	0.47	11.0	5.0 × 5.2 × 3.0
	0.75	9.7	5.0 × 5.2 × 3.0

Note: \*<sup>1</sup> 30% change

- Small size inductor for RAA207702GBM

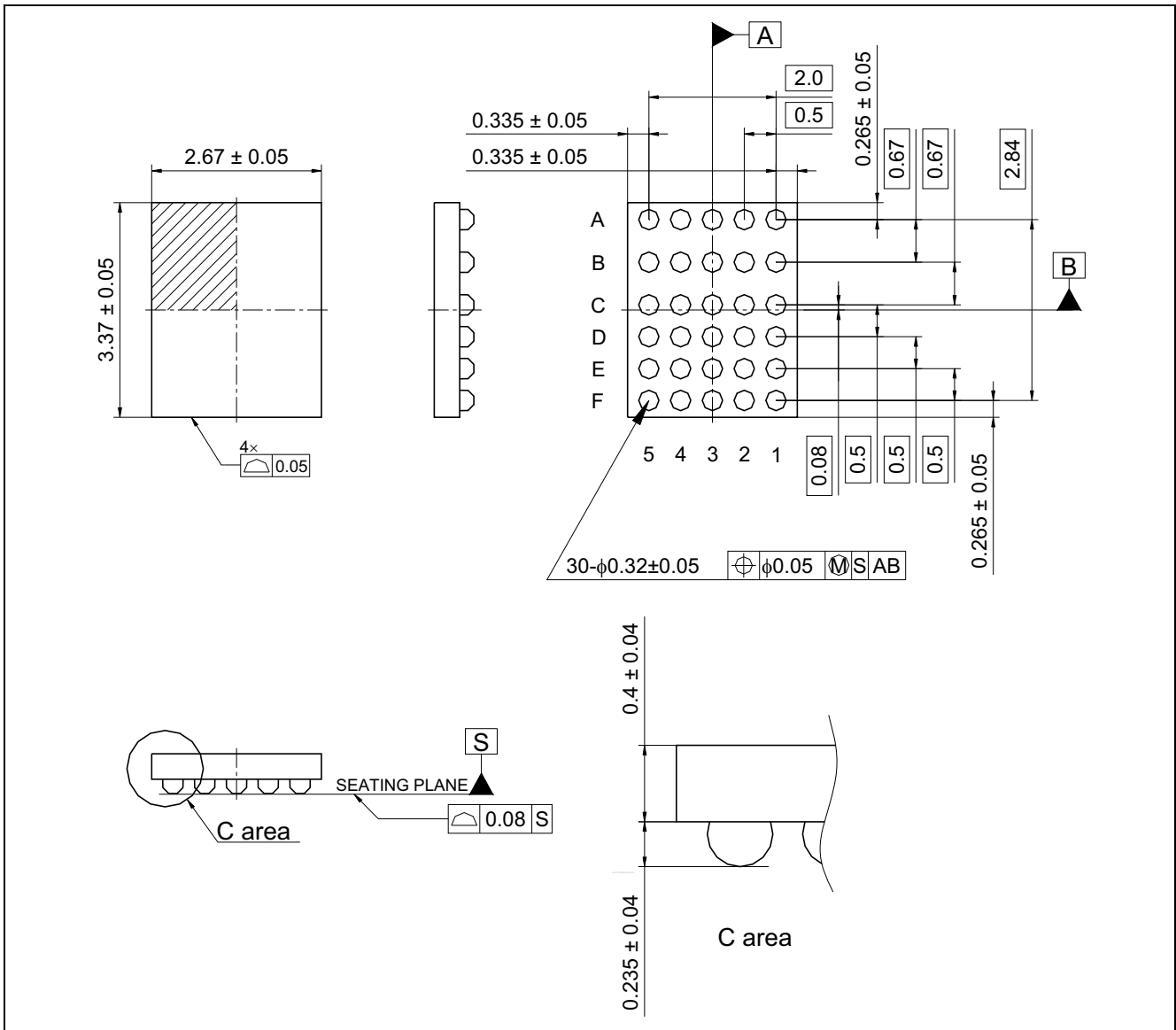
Maker	Inductance [ $\mu\text{H}$ ]	$\Delta\text{L}/\text{L}_0 = 30\%$ Change [A]	Dimensions [mm]
TOKO FDSD0420 series	0.68	8.3	4.2 × 4.2 × 2.0
	1.0	6.8	4.2 × 4.2 × 2.0
	1.5	5.7	4.2 × 4.2 × 2.0
TDK SPM4012 series	0.47	8.3	4.4 × 4.1 × 1.2
	1.0	4.8	4.4 × 4.1 × 1.2

## Representative Output Capacitors

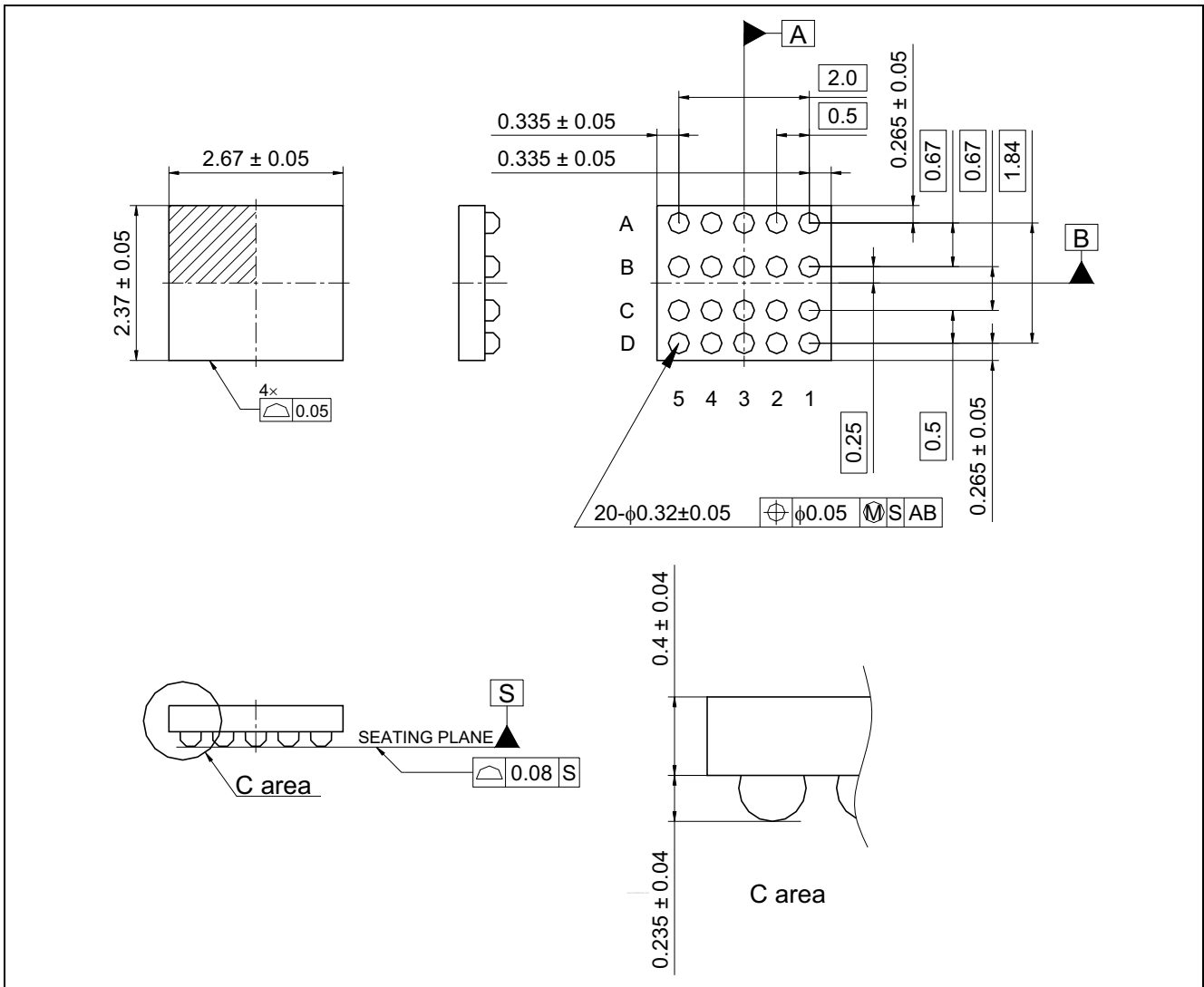
Maker	Maximum Voltage [V]	Capacitance [ $\mu\text{F}$ ]
Sanyo POSCAP series	2.0 to 10	47 to 330
Sanyo OS-CON series	2.0 to 10	47 to 330
Murata MLCC series	6.3 to 10	22 to 47
TDK MLCC series	6.3 to 10	22 to 47
TAIYO YUDEN MLCC series	6.3 to 10	22 to 47



- RAA207704GBM



- RAA207705GBM



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